# Product Preview

# PWM Voltage Mode Controller

The NCP1209P series is an enhanced version of the MC44608P series. It is a high performance voltage mode controller designed for fly-back SMPS.

These 2 series are pin to pin compatible. The device is a Power MOSFET driver offering a discrete approach (controller + discrete MOSFET) for building an offline SMPS.

It features a very high efficiency stand—by management consisting in a fully controlled and adaptable Pulsed Mode operation working in conjunction with a secondary reconfiguration.

#### **Features**

- 45 kHz, 65 kHz, 77 kHz
- 7% Frequency Accuracy Over the Whole Temp Range
- Extended V<sub>CC</sub> Working Range 8.6 V to 16 V
- Programmable Stand-by Burst Duty Cycle
- Stand-by Mode Selection from the Secondary Side of the SMPS
- 5 mA VHV Start-up Current Source
- Device Inhibition Through Start-up Current Source Reduction

## **Typical Applications**

- Energy Management in Set Top Box
- Opto Feed-back Offline SMPS
- SMPS Using a Secondary Reconfiguration for the Stand-by Mode
- Ability to Adapt the MOSFET Gate Drive
- All General Purpose Fly-back SMPS

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.



# ON Semiconductor™

http://onsemi.com

# SMPS CONTROLLER WITH ENHANCED STAND-BY MANAGEMENT

## MARKING DIAGRAMS



SO-8 CASE 751 PLASTIC





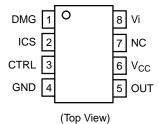
DIP-8 CASE 626 PLASTIC



xx = Specific Device Code A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week

#### **PIN CONNECTIONS**



#### **ORDERING INFORMATION**

Device	Package	Shipping
NCP1209P45	TBD	TBD
NCP1209P65	TBD	TBD
NCP1209P77	TBD	TBD

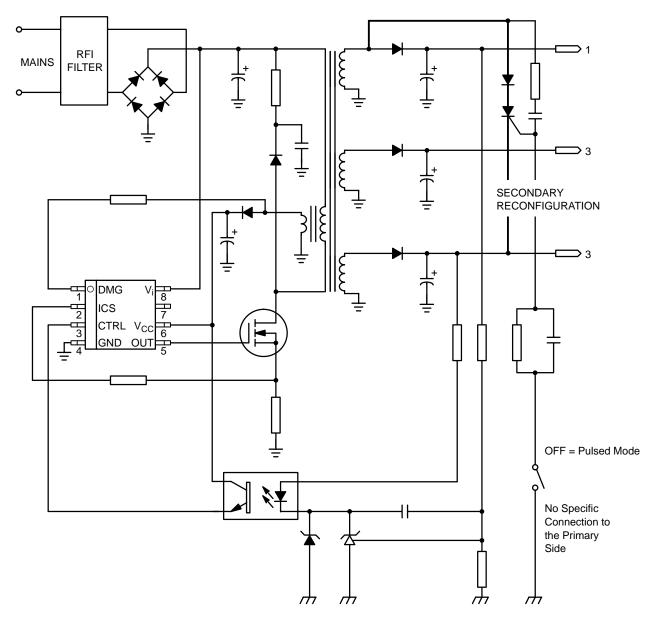


Figure 1. Typical Application Example

# **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
V <sub>CC</sub> voltage	V <sub>CC</sub>	18	V
Pin 3 sink and source current	I <sub>pin3</sub>	±3	mA
VHV pin8 voltage	V <sub>pin8</sub>	500	V
Total power supply current	I <sub>cc</sub>	20	mA
All inputs except Vi	V <sub>inputs</sub>	-1.0 to +16	V
Power dissipation and Thermal characteristics Thermal Resistance, Junction to Air PDIP Thermal Resistance, Junction to Air SOIC Maximum power dissipation at $T_A = 85^{\circ}\text{C}$ PDIP Maximum power dissipation at $T_A = 85^{\circ}\text{C}$ SOIC	R <sub>0JA</sub> R <sub>0JA</sub> P <sub>D</sub> P <sub>D</sub>	100 178 600 365	°C/W °C/W mW mW
Operating Junction Temperature	TJ	150	°C
Operating Ambient Temperature	T <sub>A</sub>	-25 to +85	°C

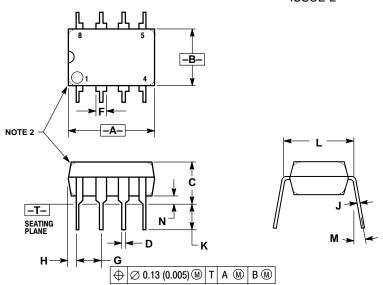
Characteristic	Symbol	Min	Тур	Max	Unit
Output Section					
Output Resistor Sink Source	R <sub>OL</sub> R <sub>OH</sub>	5 -	8.5 15	15 -	W
Output Voltage Rise Time (from 3 V up to 8 V)	t <sub>r</sub>	_	50	-	ns
Output Voltage Falling Edge Slew–Rate (from 8 V down to 3 V)	t <sub>f</sub>	-	50	-	ns
Control Input Section					
Duty Cycle @ I <sub>pin3</sub> = 450 μA	D <sub>450 μA</sub>	-	-	0	%
Duty Cycle @ I <sub>pin3</sub> = 225 μA	D <sub>225 μA</sub>	TBD	43	TBD	%
Control Input Clamp Voltage (Switching phase) @ I <sub>pin3</sub> = -225 μA	V <sub>shunt</sub>	4.65	4.9	5.15	V
Latched-off Phase Control Input (stand-by) @ I <sub>pin3</sub> = 75 μA	V <sub>LP-STBY</sub>	-	TBD	-	V
Latched-off Phase Control Input (stand-by) @ I <sub>pin3</sub> = 37 μA	V <sub>LP-STBY</sub>	-	TBD	-	V
Internal Pin3 Resistance	R <sub>int3</sub>	TBD	2	TBD	kΩ
(I <sub>supply</sub> – I <sub>CC</sub> ) / I <sub>pin3</sub> (75 μA)	K3(75)	-	20	-	-
(I <sub>supply</sub> – I <sub>CC</sub> ) / I <sub>pin3</sub> (75 μA)	K3(37)	-	20	-	-
Current Sense Section					
Maximum Sense Input Threshold	V <sub>CS-th</sub>	0.9	1.0	1.05	V
Input Bias Current	I <sub>B-cs</sub>	-1.8	-	+1.8	mA
Current Sense Source Current during Start-up Phase	I <sub>CS-stup</sub>	180	200	220	mA
Stand-by Current Sense Input Current	I <sub>CS-stby</sub>	97	100	103	mA
LEB + Propagation Delay (P45)	T <sub>DLY</sub>	TBD	TBD	TBD	ns
LEB + Propagation Delay (P65)	T <sub>DLY</sub>	TBD	TBD	TBD	ns
LEB + Propagation Delay (P77)	T <sub>DLY</sub>	TBD	350	TBD	ns
Current Sense Propagation Delay (Pin2 to OUT) (P45)	T <sub>prg</sub>	TBD	TBD	TBD	ns
Current Sense Propagation Delay (Pin2 to OUT) (P65)	T <sub>prg</sub>	TBD	TBD	TBD	ns
Current Sense Propagation Delay (Pin2 to OUT) (P77)	T <sub>prg</sub>	TBD	175	TBD	ns
Leading Edge Blanking T <sub>DLY</sub> – T <sub>prg</sub> (P45)	T <sub>LEB</sub>	-	TBD	-	ns
Leading Edge Blanking T <sub>DLY</sub> – T <sub>prg</sub> (P65)	T <sub>LEB</sub>	-	TBD	-	ns
Leading Edge Blanking T <sub>DLY</sub> – T <sub>prg</sub> (P77)	T <sub>LEB</sub>	-	TBD	-	ns
Oscillator Section					
Normal Operation Frequency (P45)	f <sub>osc</sub>	41.8	45	48.1	kHz
Normal Operation Frequency (P65)	f <sub>osc</sub>	60.45	65	69.55	kHz
Normal Operation Frequency (P77)	f <sub>osc</sub>	71.6	77	82.4	kHz
Maximum Duty Cycle @ f = f <sub>OSC</sub>	d <sub>max</sub>	76	80	84	%
Overvoltage Section					
OVP threshold level on V <sub>CC</sub>	V <sub>cc-ovp</sub>	15.9	16.4	16.9	V

**ELECTRICAL CHARACTERISTICS** (V<sub>CC</sub> = 10 V, T<sub>J</sub> = 0°C up 105°C, Output Loaded with 1 nF)

Characteristic	Symbol	Min	Тур	Max	Unit
Demagnetisation Detection Section					
Demag Comparator Threshold (V <sub>pin1</sub> decreasing)	V <sub>dmg-th</sub>	45	50	55	mV
Demag Comparator Hysteresis	H <sub>dmg</sub>	_	30	-	mV
Propagation Delay (Input to Output, Low to High)	T <sub>PHL(In/Out)</sub>	_	300	-	ns
Input Bias Current (V <sub>demag</sub> = 50mV)	I <sub>dem-lb</sub>	-0.6	-	-	mA
Negative Clamp Level @ I <sub>demag</sub> = 50 μA	V <sub>cl-neg-dem</sub>	-0.9	-0.7	-0.4	V
Positive Clamp Level @ I <sub>demag</sub> = 50 μA	V <sub>cl-pos dem</sub>	9	10	11	V
Overtemperature Section					
Overtemp		_	150	-	°C
Normal Mode Recovery Section					
Demagnetisation Voltage for Normal Mode Recovery	Vdem NM	2.38	2.4	2.52	V
Supply Section					
Start-up Voltage	$V_{\text{stup}}$	11.8	12.4	13	V
Output Disabling V <sub>CC</sub>	V <sub>uvlo1</sub>	8.2	8.6	9	V
V <sub>CC</sub> Voltage for Istart–up activation	V <sub>uvlo2</sub>	5.03	5.3	5.5	V
1 <sup>st</sup> level start–up HV Current Source @ V <sub>CC</sub> < 1.5 V	I <sub>CC1</sub>	100	200	300	mA
2 <sup>nd</sup> level start-up HV Current Source @ V <sub>CC</sub> > 3 V	I <sub>CC2L</sub>	3.2	4.2	4.8	mA
2 <sup>nd</sup> level start-up HV Current Source @ V <sub>CC</sub> = 10 V	I <sub>CC2H</sub>	2.2	3.2	3.8	mA
Start-up Current Source Leakage	I <sub>stup Ik</sub>	_	70	-	mA
I <sub>CC</sub> when Switching (P45)	I <sub>ccs</sub>	TBD	_	TBD	mA
I <sub>CC</sub> when Switching (P65)	Iccs	TBD	-	TBD	mA
I <sub>CC</sub> when Switching (P77)	Iccs	2.2	2.6	3	mA
I <sub>CC</sub> in the Latched Off Phase	Iccoff	350	500	650	mA
Hiccup Mode Duty Cycle	D <sub>hiccup</sub>	_	12.5	-	%

# **PACKAGE DIMENSIONS**

DIP-8 CASE 626-05 ISSUE L

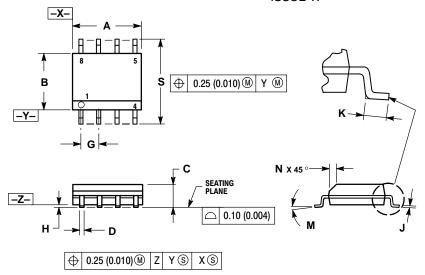


- NOTES:
  1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
  2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
  3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
С	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300 BSC	
M		10°		10°
N	0.76	1.01	0.030	0.040

# **PACKAGE DIMENSIONS**

## SO-8 CASE 751-07 ISSUE W



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.

  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6 20	0.228	0 244

# **Notes**

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

#### **PUBLICATION ORDERING INFORMATION**

#### Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

**Phone:** 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax:** 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

**JAPAN**: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031

Phone: 81–3–5740–2700 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.